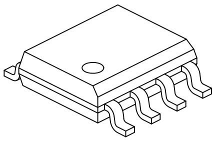
Dual N-Channel High Density Trench MOSFET (20V, 6.0A)

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(on)}$ (m-ohm) Max
20V	6.0A	28 @ V_{GS} =4.5V, ID=6.0A
		40 @ V_{GS} =2.5V, ID=5.2A

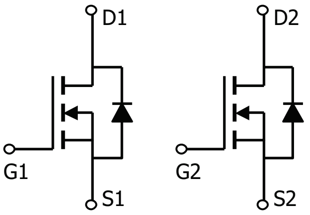
Features

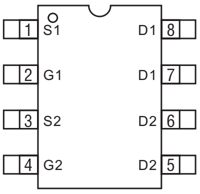
- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Lead free product is acquired
- Surface mount Package

Pin information:



SOP-8





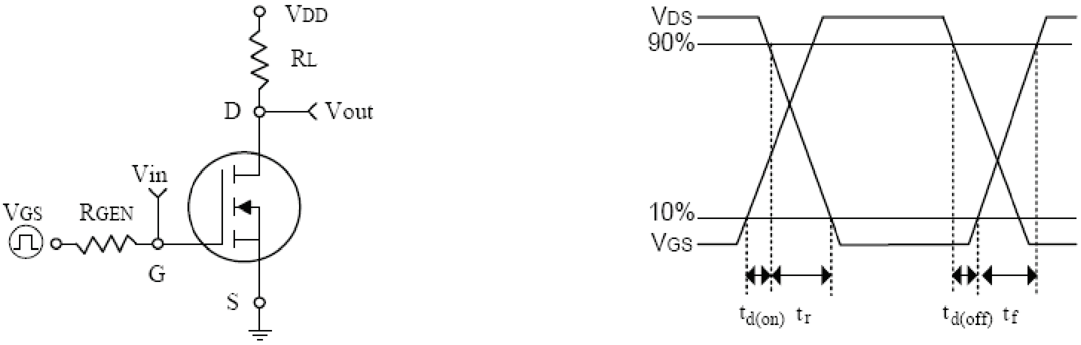
Top view
SOP-8

Pin Number SOP-8	Pin Name	Function
1	S1	Source2
2	G1	Gate2
3	S2	Source1
4	G2	Gate1
5	D2	Drain1
6	D2	Drain1
7	D1	Drain2
8	D1	Drain2

Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current (Continuous)	6.0	A
I_{DM}	Drain Current (Pulsed) [a]	20	A
P_D	Total Power Dissipation @T_A=25°C	2.0	W
I_S	Maximum Diode Forward Current	1.7	A
T_j, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (PCB mounted)[b]	62	°C/W

a: Repetitive Rating: Pulse width limited by the maximum junction temperation.
b: 1-in^2 2oz Cu PCB board



Switching Test Circuit and Switching Waveforms